



EXPRESS MAIL NO. EV449556792US

Sheet 1 of 1

FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 854163.410	APPLICATION NO. 10/782,737
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANTS Osama Khouri et al.	
		FILING DATE February 18, 2004	GROUP ART UNIT 2818 24

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PL	AA	5,883,827	03/16/99	Morgan	365	100	
PL	AB	5,694,356	12/02/97	Wong et al.	365	185.03	
PL	AC	6,141,253	10/31/00	Lin	365	185.28	
PL	AD	6,487,113	11/26/02	Park et al.	365	163	
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
PL	AK	63-42097	02/23/88	JP (+ Abstract in English)	✓	
	AL					
	AM					
	AN					
	AO					

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

PL	AP	Hwang, Y. et al., "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," in <i>Proceedings of the Non-Volatile Semiconductor Memory Workshop NVMW 2003</i> , Monterey, CA., February 16-20, 2003, pp. 91-92.
	AQ	
	AR	

EXAMINER PHO m. Luu	DATE CONSIDERED 2/17/2005
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* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).